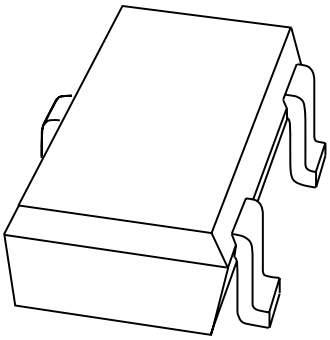
DATA SHEET



PBSS5140U

40 V low V_{CEsat} PNP transistor

Product data sheet
Supersedes data of 2001 Mar 27

2001 Jul 20

40 V low V_{CEsat} PNP transistor PBSS5140U

FEATURES

- Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation
- Enhanced performance over SOT23 1A standard packaged transistor.

APPLICATIONS

- General purpose switching and muting
- LCD back lighting
- Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

DESCRIPTION

PNP low V_{CEsat} transistor in a SOT323 (SC-70) plastic package.

MARKING

TYPE NUMBER	MARKING CODE
PBSS5140U	51t

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	−40	V
I_{CM}	peak collector current	−2	A
R_{CEsat}	equivalent on-resistance	<500	mΩ

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

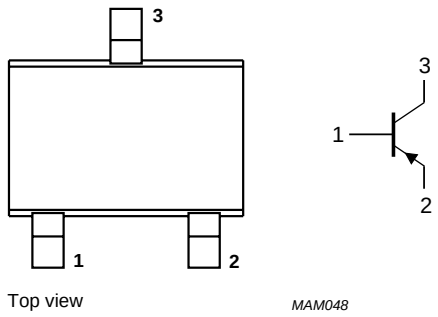


Fig.1 Simplified outline (SOT323; SC-70) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	−40	V
V_{CEO}	collector-emitter voltage	open base	–	−40	V
V_{EBO}	emitter-base voltage	open collector	–	−5	V
I_C	collector current (DC)		–	−1	A
I_{CM}	peak collector current		–	−2	A
I_{BM}	peak base current		–	−1	A
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	250	mW
		$T_{amb} \leq 25$ °C; note 2	–	350	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Notes

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm^2.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	in free air; note 1	500	K/W
		in free air; note 2	357	K/W

Notes

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm^2.

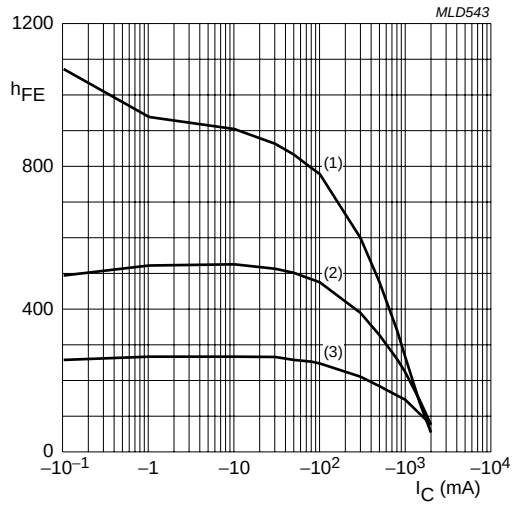
CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	V_{CB} = –40 V; I_C = 0	–	–	–100	nA
		V_{CB} = –40 V; I_C = 0; T_{amb} = 150 °C	–	–	–50	μA
I_{CEO}	collector-emitter cut-off current	V_{CE} = –30 V; I_B = 0	–	–	–100	nA
I_{EBO}	emitter-base cut-off current	V_{EB} = –5 V; I_C = 0	–	–	–100	nA
h_{FE}	DC current gain	V_{CE} = –5 V; I_C = –1 mA	300	–	–	
		V_{CE} = –5 V; I_C = –100 mA	300	–	800	
		V_{CE} = –5 V; I_C = –500 mA	250	–	–	
		V_{CE} = –5 V; I_C = –1 A	160	–	–	
V_{CEsat}	saturation voltage	I_C = –100 mA; I_B = –1 mA	–	–	–200	mV
		I_C = –500 mA; I_B = –50 mA	–	–	–250	mV
		I_C = –1 A; I_B = –100 mA	–	–	–500	mV
R_{CEsat}	equivalent on-resistance	I_C = –500 mA; I_B = –50 mA; note 1	–	300	<500	mΩ
V_{BEsat}	base-emitter saturation voltage	I_C = –1 A; I_B = –50 mA	–	–	–1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = –5 V; I_C = –1 A	–	–	–1	V
f_T	transition frequency	I_C = –50 mA; V_{CE} = –10 V; f = 100 MHz	150	–	–	MHz
C_c	collector capacitance	V_{CB} = –10 V; I_E = I_e = 0; f = 1 MHz	–	–	12	pF

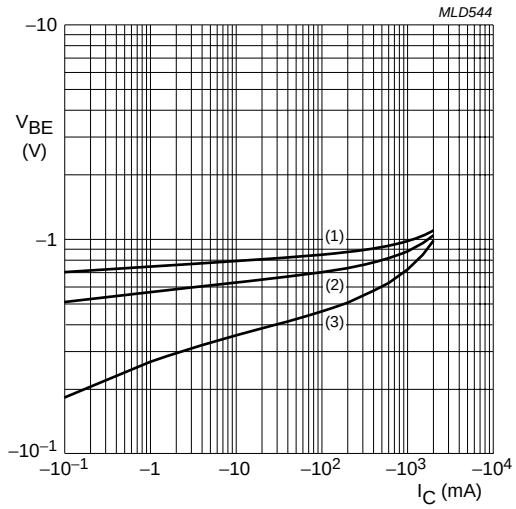
Note

1. Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.



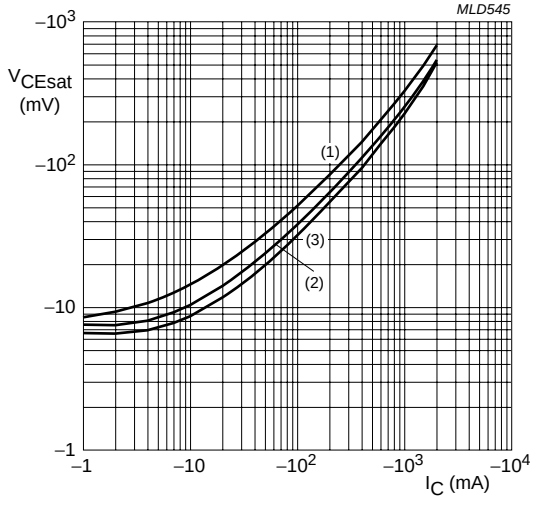
V_{CE} = −5 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.2 DC current gain as a function of collector current; typical values.



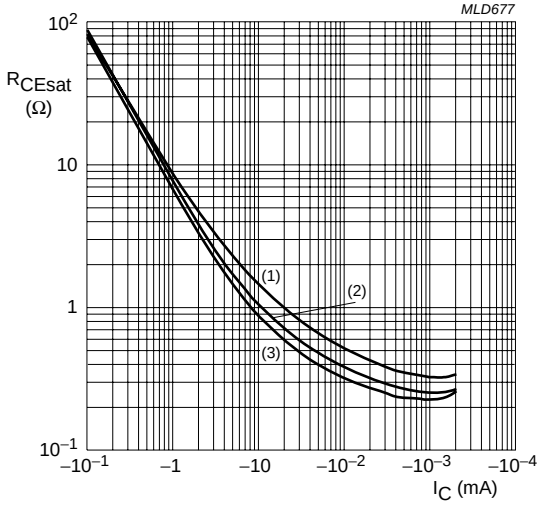
V_{CE} = −5 V.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.3 Base-emitter voltage as a function of collector current; typical values.



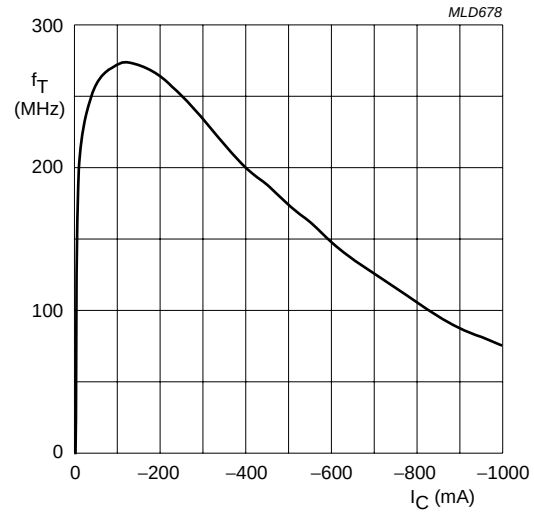
I_C/I_B = 10.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



I_C/I_B = 10.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.5 Equivalent on-resistance as a function of collector current; typical values.

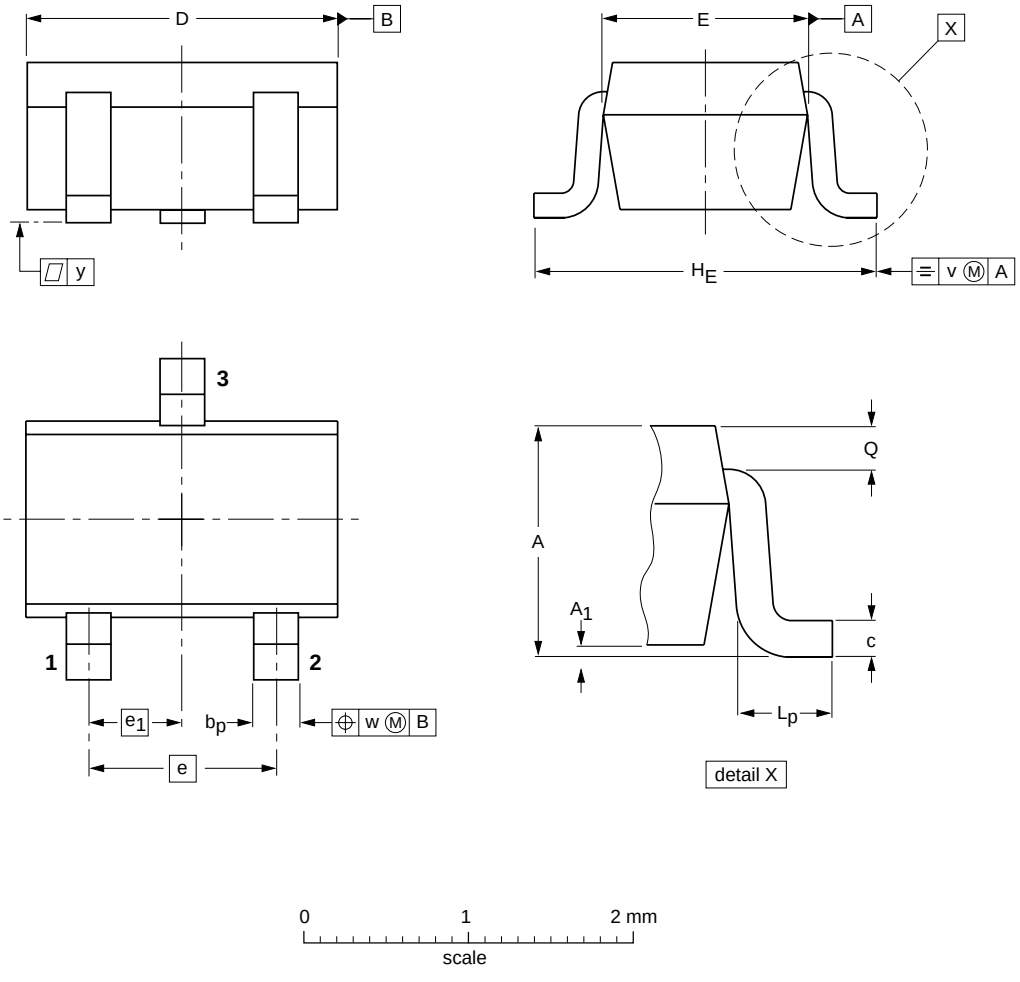


V_{CE} = −10 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.6 Transition frequency as a function of collector current; typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT323**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

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